

**AMENDMENTS TO THE CLAIMS:**

**Please cancel claims 10-11 without prejudice or disclaimer and amend the claims as follows:**

1. (Currently Amended) A method of producing a semiconductor crystal of a Group III nitride compound semiconductor ~~and independent of a starting substrate~~, said method comprising:

laminating a seed monolayer or multilayer on ~~said a~~ starting substrate;

chemically or physically etching part of a seed layer-forming surface of said starting substrate to thereby partially or dispersively leave said seed layer as a plurality of non-etched portions on said starting substrate;

growing said semiconductor crystal on exposed surfaces of said non-etched portions of said seed layer as initial crystal growth surfaces for starting growth of said semiconductor crystal until said crystal growth surfaces are connected to one another by crystal growth so as to be provided as at least one series of approximately flat surfaces; and

breaking said non-etched portions to thereby separate said semiconductor crystal from said starting ~~substrate~~; substrate.

wherein the crystal growing ~~step~~ is performed by a halide vapor phase epitaxy method in the condition that a supply ratio of a Group V material to a Group III material is in a range of from 30 to 80, both inclusively.

2. (Currently Amended) A method of producing a semiconductor crystal according to claim 1, wherein a thickness of said semiconductor crystal in the crystal growing ~~step~~ is not smaller than 50  $\mu\text{m}$ .

3. (Original) A method of producing a semiconductor crystal according to claim 1, wherein said semiconductor crystal and said starting substrate are cooled or heated to generate stress based on a difference between a thermal expansion coefficient of said semiconductor crystal and a thermal expansion coefficient of said starting substrate to break said non-etched portions by said stress.

4. (Currently Amended) A method of producing a semiconductor crystal according to claim 1, wherein said seed monolayer or an uppermost layer of said seed multilayer ~~is made of~~ comprises gallium nitride (GaN).

5. (Currently Amended) A method of producing a semiconductor crystal according to claim 1, wherein said seed monolayer or a lowermost layer of said seed multilayer ~~is made of~~ comprises aluminum nitride (AlN).

6. (Currently Amended) A method of producing a semiconductor crystal according to claim 1, wherein an interval for arrangement of said non-etched portions in the non-etched portion forming ~~step~~ is selected to be in a range of from 1  $\mu\text{m}$  to 50  $\mu\text{m}$ , both inclusively.

7. (Currently Amended) A method of producing a semiconductor crystal according to claim 1, wherein said starting substrate is etched by  $0.01\ \mu\text{m}$  or deeper in the non-etched portion forming ~~step~~.

8. (Currently Amended) A method of producing a semiconductor crystal according to claim 1, wherein a lateral thickness, width or diameter of each of said non-etched portions in the non-etched portion forming ~~step~~ is selected to be in a range of from  $0.1\ \mu\text{m}$  to  $20\ \mu\text{m}$ , both inclusively.

9. (Currently Amended) A method of producing a semiconductor crystal according to claim 1, further comprising ~~the rest removing step of~~ removing the broken rest of said non-etched portions remaining on a rear surface of said semiconductor crystal by a chemical or physical process ~~such as etching~~ at least after the separating ~~step~~.

10. (Canceled)

11. (Canceled)

12. (New) The method of claim 9, wherein said chemical or physical process comprises etching.